

ABSTRACT OF THE DISCLOSURE

A method for repairing a memory comprising a Memory Built-In Self Repair (MBISR) structure comprises the steps of detection of defective storage cells, and redundancy allocation. The redundancy allocation step is carried out in such a way that it combines a row and/or column oriented redundancy repair approach with a word oriented redundancy repair approach. A Memory Built-In Self Repair (MBISR) device comprises at least one memory (2) with row and/or column redundancy, at least one row and/or column Memory Built-In Self Repair (MBISR) circuit (3), and a word redundancy block (4). Furthermore, a distributed MBISR structure as well as dedicated Column/Row MBISR circuits (3) are provided.